

2SC4913

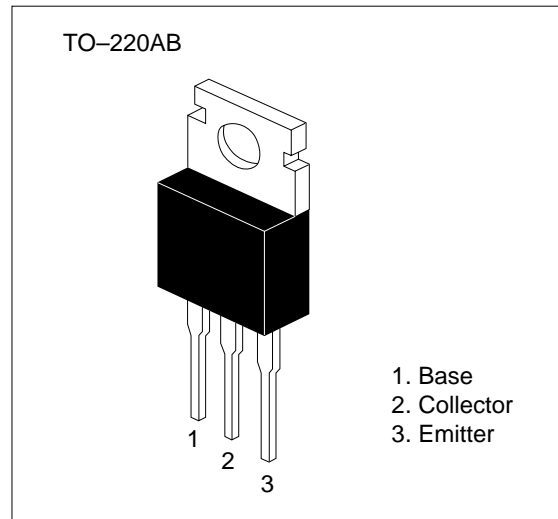
Silicon NPN Triple Diffused

Application

High voltage amplifier

Features

High breakdown voltage
 $V_{(BR)CEO} = 2000 \text{ V min}$



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

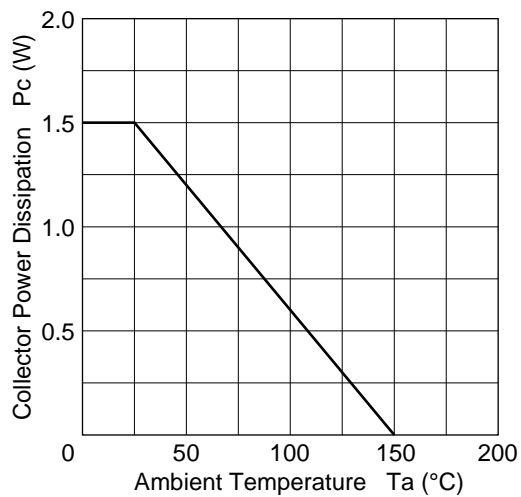
Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	2000	V
Collector to emitter voltage	V_{CEO}	2000	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	20	mA
Collector peak current	$i_{c(\text{peak})}$	40	mA
Collector power dissipation	P_C	1.5	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

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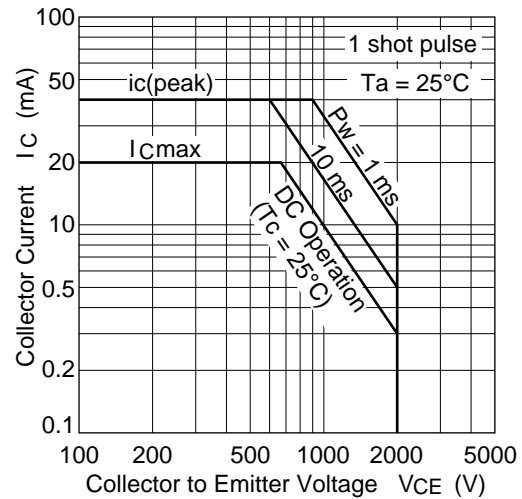
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector cutoff current	I_{CES}	—	—	500	μA	$V_{CE} = 2000\text{ V}$, $R_{BE} = 0$
Collector cutoff current	I_{CEO}	—	—	5	mA	$V_{CE} = 2000\text{ V}$, $R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	500	μA	$V_{EB} = 6\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}	10	—	—		$V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5.0	V	$I_C = 10\text{ mA}$, $I_B = 2\text{ mA}$

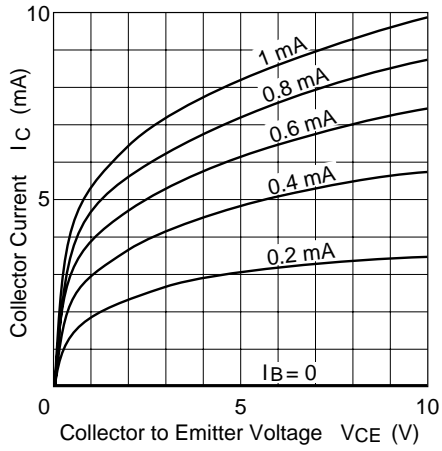
Maximum Collector Power Dissipation Curve



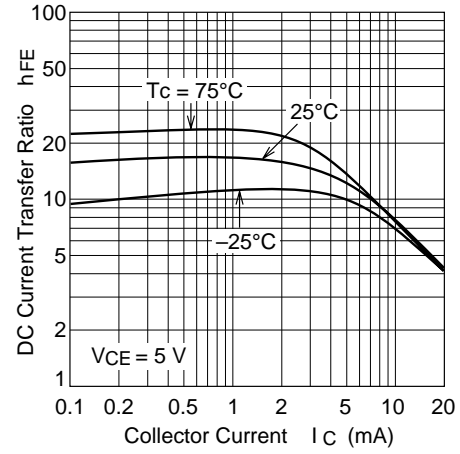
Area of Safe Operation



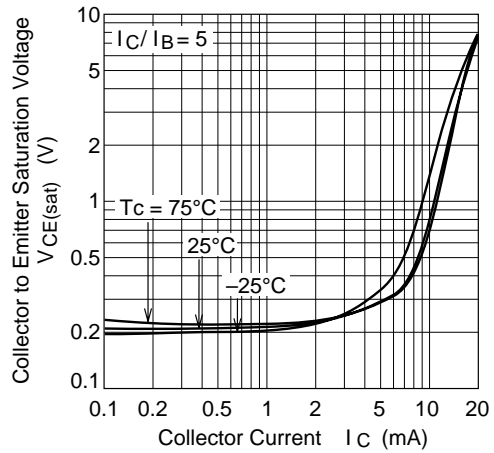
Typical Output Characteristics



DC Current Transfer Ratio vs. Collector Current



Collector to Emitter Saturation Voltage vs. Collector Current



Base to Emitter Saturation Voltage vs. Collector Current

